

**COMPLEMENTARY SILICON  
HIGH-POWER TRANSISTORS**

General-Purpose Power Amplifier and Switching Applications

<b>PNP</b>	<b>NPN</b>
<b>2N5883</b>	<b>2N5885</b>
<b>2N5884</b>	<b>2N5886</b>

**FEATURES:**

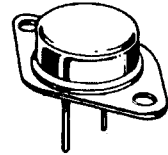
- \* Low Collector-Emitter Saturation Voltage -  
 $V_{CE(SAT)} = 1.0V(\text{Max.}) @ I_C = 15 A$
- \* Excellent DC Current Gain -  
 $hFE = 20 \sim 100 @ I_C = 10 A$

**Boca Semiconductor Corp.**  
**BSC**  
<http://www.bocasemi.com>

**MAXIMUM RATINGS**

Characteristic	Symbol	2N5883 2N5885	2N5884 2N5886	Unit
Collector-Emitter Voltage	$V_{CEO}$	60	80	V
Collector-Base Voltage	$V_{CBO}$	60	80	V
Emitter-Base Voltage	$V_{EBO}$	5.0		V
Collector Current-Continuous -Peak	$I_C$ $I_{CM}$		25 50	A
Base Current	$I_B$	7.5		A
Total Power Dissipation @ $T_C = 25^\circ C$ Derate above $25^\circ C$	$P_D$	200 1.15		W W/ $^\circ C$
Operating and Storage Junction Temperature Range	$T_J, T_{STG}$	- 65 to +200		$^\circ C$

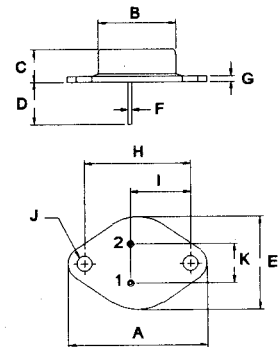
**25 AMPERE  
COMPLEMENTARY SILICON  
POWER TRANSISTORS**  
60 - 80 Volts  
200 Watts



**TO-3**

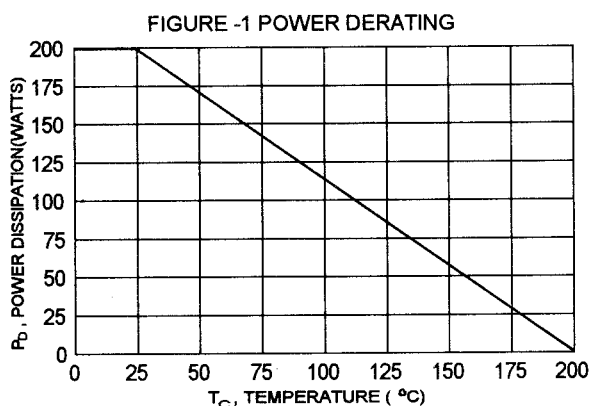
**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance Junction to Case	$R_{\theta jc}$	0.875	$^\circ C/W$



PIN 1.BASE  
2.EMITTER  
COLLECTOR(CASE)

DIM	MILLIMETERS	
	MIN	MAX
A	38.75	39.96
B	19.28	22.23
C	7.96	9.28
D	11.18	12.19
E	25.20	26.67
F	0.92	1.09
G	1.38	1.62
H	29.90	30.40
I	16.64	17.30
J	3.88	4.36
K	10.67	11.18



**ELECTRICAL CHARACTERISTICS (  $T_c = 25^\circ\text{C}$  unless otherwise noted )**

Characteristic	Symbol	Min	Max	Unit
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**OFF CHARACTERISTICS**

Collector - Emitter Sustaining Voltage (1) ( $I_c = 200\text{ mA}$ , $I_B = 0$ )	2N5883, 2N5885 2N5884, 2N5886	$V_{CEO(sus)}$	60 80	V
Collector Cutoff Current ( $V_{CE} = 30\text{ V}$ , $I_B = 0$ ) ( $V_{CE} = 40\text{ V}$ , $I_B = 0$ )	2N5883, 2N5885 2N5884, 2N5886	$I_{CEO}$	2.0 2.0	mA
Collector Cutoff Current ( $V_{CE} = 60\text{ V}$ , $V_{BE(off)} = 1.5\text{ V}$ ) ( $V_{CE} = 80\text{ V}$ , $V_{BE(off)} = 1.5\text{ V}$ ) ( $V_{CE} = 60\text{ V}$ , $V_{BE(off)} = 1.5\text{ V}$ , $T_c = 150^\circ\text{C}$ ) ( $V_{CE} = 80\text{ V}$ , $V_{BE(off)} = 1.5\text{ V}$ , $T_c = 150^\circ\text{C}$ )	2N5883, 2N5885 2N5884, 2N5886 2N5883, 2N5885 2N5884, 2N5886	$I_{CEX}$	1.0 1.0 10 10	mA
Collector Cutoff Current ( $V_{CB} = 60\text{ V}$ , $I_E = 0$ ) ( $V_{CB} = 80\text{ V}$ , $I_E = 0$ )	2N5883, 2N5885 2N5884, 2N5886	$I_{CBO}$	1.0 1.0	mA
Emitter Cutoff Current ( $V_{EB} = 5.0\text{ V}$ , $I_C = 0$ )		$I_{EBO}$	1.0	mA

**ON CHARACTERISTICS (1)**

DC Current Gain ( $I_c = 3.0\text{ A}$ , $V_{CE} = 4.0\text{ V}$ ) ( $I_c = 10\text{ A}$ , $V_{CE} = 4.0\text{ V}$ ) ( $I_c = 25\text{ A}$ , $V_{CE} = 4.0\text{ V}$ )		$h_{FE}$	35 20 4.0	100
Collector-Emitter Saturation Voltage ( $I_c = 15\text{ A}$ , $I_B = 1.5\text{ A}$ ) ( $I_c = 25\text{ A}$ , $I_B = 6.25\text{ A}$ )		$V_{CE(sat)}$		1.0 4.0
Base-Emitter On Voltage ( $I_c = 10\text{ A}$ , $V_{CE} = 4.0\text{ V}$ )		$V_{BE(on)}$		1.5
Base-Emitter Saturation Voltage ( $I_c = 25\text{ A}$ , $I_B = 6.25\text{ A}$ )		$V_{BE(sat)}$		2.5

**DYNAMIC CHARACTERISTICS**

Current-Gain-Bandwidth Product (2) ( $I_c = 1.0\text{ A}$ , $V_{CE} = 10\text{ V}$ , $f = 1.0\text{ MHz}$ )		$f_T$	4.0	MHz
Small-Signal Current Gain ( $I_c = 3.0\text{ A}$ , $V_{CE} = 4.0\text{ V}$ , $f = 1.0\text{ KHz}$ )		$h_{fe}$	20	

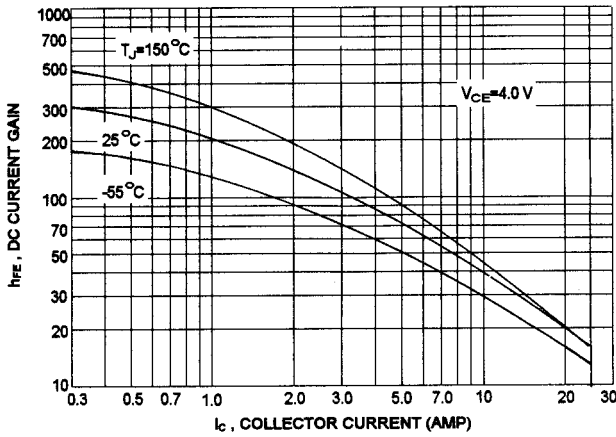
(1) Pulse Test: Pulse width  $\leq 300\text{ us}$ , Duty Cycle  $\leq 2.0\%$ (2)  $f_T = |h_{fe}| \cdot f_{test}$ 

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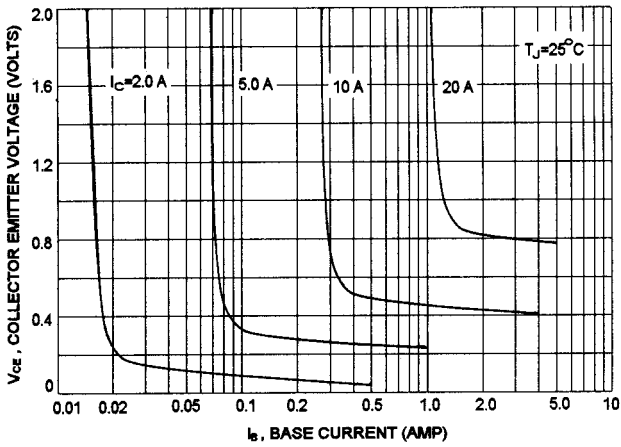
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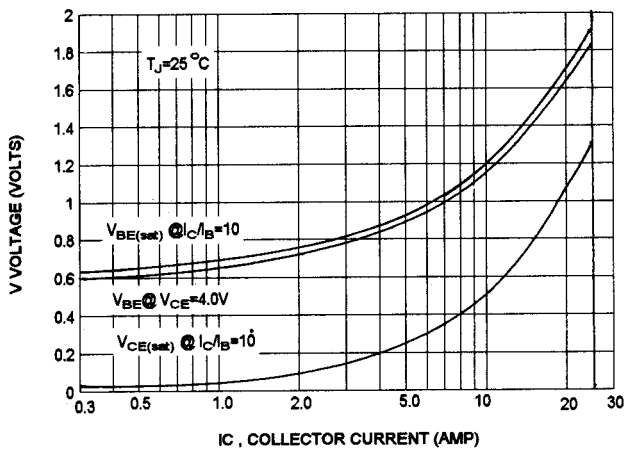
PNP 2N5883,2N5884  
DC CURRENT GAIN



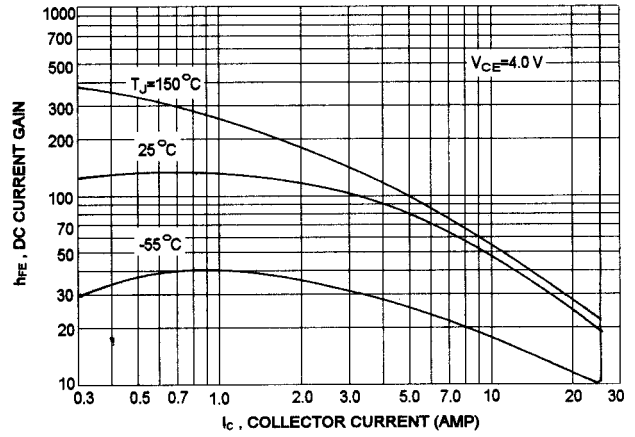
COLLECTOR SATURATION REGION



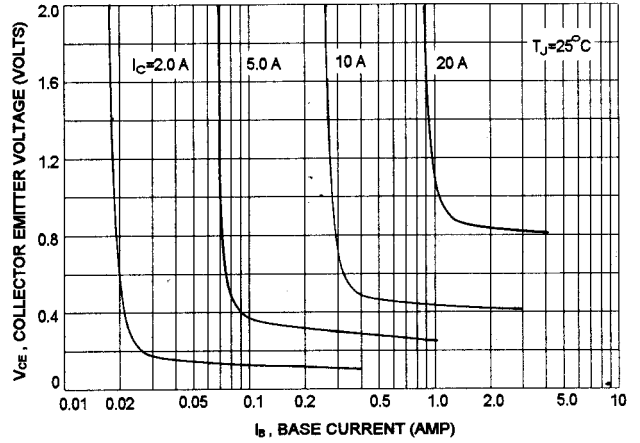
"ON" VOLTAGES



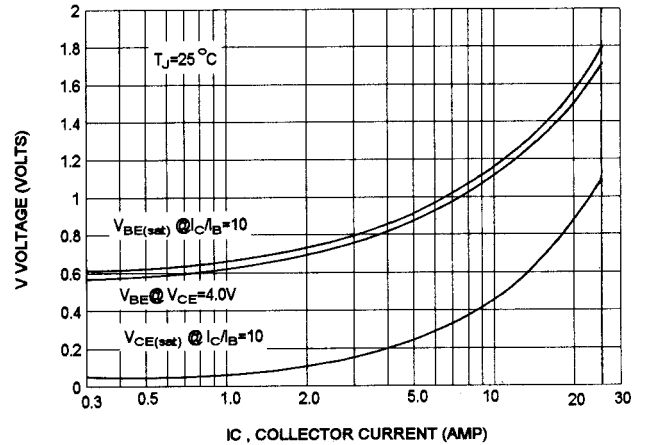
NPN 2N5885,2N5886  
DC CURRENT GAIN



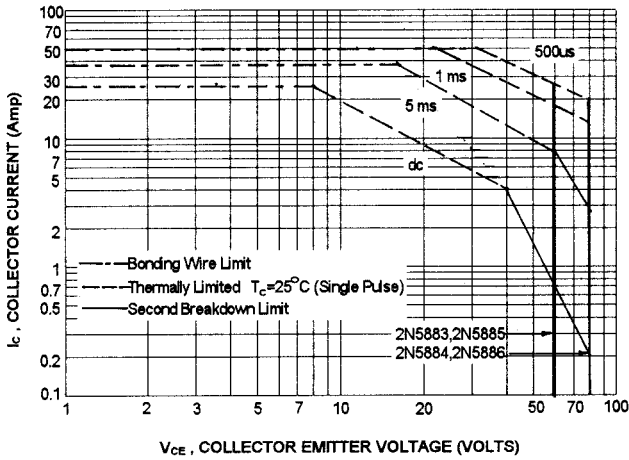
COLLECTOR SATURATION REGION



"ON" VOLTAGES



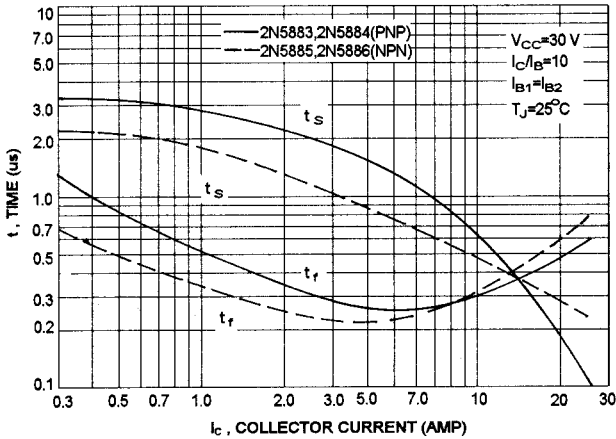
ACTIVE-REGION SAFE OPERATING AREA (SOA)



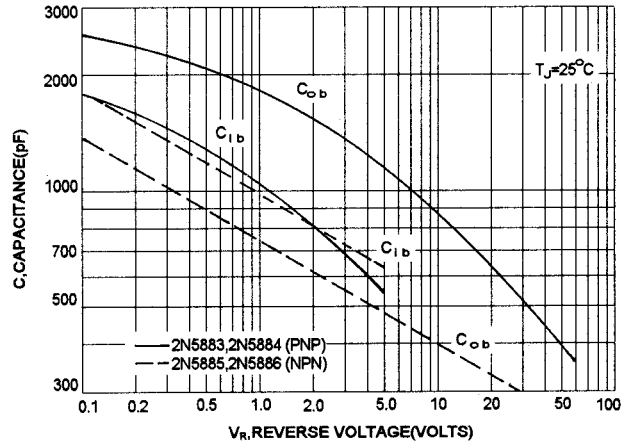
There are two limitation on the power handling ability of a transistor: average junction temperature and second breakdown safe operating area curves indicate  $I_C$ - $V_{CE}$  limits of the transistor that must be observed for reliable operation i.e., the transistor must not be subjected to greater dissipation than curves indicate.

The data of SOA curve is base on  $T_{J(PK)}=200^\circ\text{C}$ ;  $T_C$  is variable depending on conditions. second breakdown pulse limits are valid for duty cycles to 10% provided  $T_{J(PK)}\leq 200^\circ\text{C}$ . At high case temperatures, thermal limita - tion will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

TURN-OFF TIME



CAPACITANCES



TURN-ON TIME

